

# Hiroaki Ohta

## List of Publications by Year in descending order

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40  
papers

1,757  
citations

279701

23  
h-index

360920

35  
g-index

40  
all docs

40  
docs citations

40  
times ranked

1250  
citing authors

#	ARTICLE	IF	CITATIONS
1	High temperature thermoelectric properties of optimized InGaN. Journal of Applied Physics, 2011, 110, .	1.1	53
2	GaN-Based Optical Devices. , 2011, , 69-86.		0
3	The low leakage current in floating body GaN metal oxide semiconductor field effect transistors. Solid-State Electronics, 2010, 54, 1561-1565.	0.8	0
4	Plasma-surface interactions for advanced plasma etching processes in nanoscale ULSI device fabrication: A numerical and experimental study. Thin Solid Films, 2010, 518, 3461-3468.	0.8	31
5	High Quality InGaN/AlGaN Multiple Quantum Wells for Semipolar InGaN Green Laser Diodes. Applied Physics Express, 2010, 3, 082001.	1.1	62
6	30-mW-Class High-Power and High-Efficiency Blue Semipolar (10 $\bar{1}$ 1) InGaN/GaN Light-Emitting Diodes Obtained by Backside Roughening Technique. Applied Physics Express, 2010, 3, 102101.	1.1	77
7	Stacking fault formation in the long wavelength InGaN/GaN multiple quantum wells grown on m-plane GaN. Applied Physics Letters, 2010, 96, .	1.5	74
8	Optimization of Device Structures for Bright Blue Semipolar (10 $\bar{1}$ 1) Light Emitting Diodes via Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2010, 49, 070206.	0.8	19
9	Electroluminescence Characterization of (20 $\bar{1}$ 1) InGaN/GaN Light Emitting Diodes with Various Wavelengths. Japanese Journal of Applied Physics, 2010, 49, 070203.	0.8	23
10	High Power and High Efficiency Blue InGaN Light Emitting Diodes on Free-Standing Semipolar (30 $\bar{1}$ 1) Bulk GaN Substrate. Japanese Journal of Applied Physics, 2010, 49, 080203.	0.8	12
11	Propagation of Spontaneous Emission in Birefringent m-Axis Oriented Semipolar (11 $\bar{2}$ ) (Al,In,Ga)N Waveguide Structures. Japanese Journal of Applied Physics, 2010, 49, 010207.	0.8	7
12	Vertical Stand Transparent Light-Emitting Diode Architecture for High-Efficiency and High-Power Light-Emitting Diodes. Japanese Journal of Applied Physics, 2010, 49, 080210.	0.8	20
13	Optical waveguide simulations for the optimization of InGaN-based green laser diodes. Journal of Applied Physics, 2010, 107, .	1.1	57
14	InGaN/GaN Blue Laser Diode Grown on Semipolar (30 $\bar{1}$ 1) Free-Standing GaN Substrates. Applied Physics Express, 2010, 3, 052702.	1.1	27
15	Future of group-III nitride semiconductor green laser diodes [Invited]. Journal of the Optical Society of America B: Optical Physics, 2010, 27, B45.	0.9	63
16	Continuous-Wave Operation of Pure Blue AlGaN-Cladding-Free Nonpolar InGaN/GaN Laser Diodes. Applied Physics Express, 2010, 3, 092103.	1.1	27
17	m-plane pure blue laser diodes with p-GaN/n-AlGaN-based asymmetric cladding and InGaN-based wave-guiding layers. Applied Physics Letters, 2009, 95, 081110.	1.5	20
18	Field and polarity dependence of time-to-resistance increase in Fe $\alpha$ -O films studied by constant voltage stress method. Applied Physics Letters, 2009, 94, 013507.	1.5	5

#	ARTICLE	IF	CITATIONS
19	Simulation and experimental study on the characteristics of plasma-induced damage and methodology for accurate damage analysis. , 2009, , .		0
20	An Improvement of Stillingerâ€“Weber Interatomic Potential Model for Reactive Ion Etching Simulations. Japanese Journal of Applied Physics, 2009, 48, 020225.	0.8	14
21	GaN-Based Integrated Lateral Thermoelectric Device for Micro-Power Generation. Applied Physics Express, 2009, 2, 111003.	1.1	54
22	m-Plane GaN-Based Blue Superluminescent Diodes Fabricated Using Selective Chemical Wet Etching. Applied Physics Express, 2009, 2, 121004.	1.1	40
23	Nonpolar/Semipolar GaN Technology for Violet, Blue, and Green Laser Diodes. MRS Bulletin, 2009, 34, 324-327.	1.7	25
24	Numerical Study on Si Etching by Monatomic Br+/Cl+Beams and Diatomic Br2+/Cl2+/HBr+Beams. Japanese Journal of Applied Physics, 2009, 48, 070219.	0.8	8
25	Partial strain relaxation via misfit dislocation generation at heterointerfaces in (Al,In)GaN epitaxial layers grown on semipolar (112 $\bar{2}$ ) GaN free standing substrates. Applied Physics Letters, 2009, 95, .	1.5	98
26	Molecular-Dynamics-Based Profile Evolution Simulation for Sub-10-nm Si Processing Technology. Applied Physics Express, 2009, 2, 116501.	1.1	12
27	Continuous-Wave Operation of Blue Laser Diodes Based on Nonpolar m-Plane Gallium Nitride. Applied Physics Express, 2008, 1, 011102.	1.1	56
28	Vertical GaN-Based Trench Gate Metal Oxide Semiconductor Field-Effect Transistors on GaN Bulk Substrates. Applied Physics Express, 2008, 1, 011105.	1.1	186
29	Molecular Dynamics Simulation of Si Etching by Off-Normal Cl+Bombardment at High Neutral-to-Ion Flux Ratios. Japanese Journal of Applied Physics, 2008, 47, 8560-8564.	0.8	15
30	Numerical Investigation on Origin of Microscopic Surface Roughness during Si Etching by Chemically Reactive Plasmas. Japanese Journal of Applied Physics, 2008, 47, 6464-6466.	0.8	13
31	Temperature dependence of polarized photoluminescence from nonpolar m-plane InGaN multiple quantum wells for blue laser diodes. Applied Physics Letters, 2008, 92, .	1.5	78
32	Reduction in threshold voltages in GaN-based metal oxide semiconductor field effect transistors. Applied Physics Letters, 2008, 92, 243505.	1.5	5
33	Pure Blue Laser Diodes Based on Nonpolar m-Plane Gallium Nitride with InGaN Waveguiding Layers. Japanese Journal of Applied Physics, 2007, 46, L820-L822.	0.8	50
34	Temperature dependence of polarized electroluminescence from nonpolar m-plane InGaN-based light emitting diodes. Applied Physics Letters, 2007, 91, 171110.	1.5	43
35	Continuous-Wave Operation of m-Plane InGaN Multiple Quantum Well Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L187-L189.	0.8	143
36	Characteristics of Polarized Electroluminescence from m-plane InGaN-based Light Emitting Diodes. Japanese Journal of Applied Physics, 2007, 46, L1010-L1012.	0.8	40

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37	GaN-Based Trench Gate Metal Oxide Semiconductor Field Effect Transistors with Over 100 cm <sup>2</sup> /(V s) Channel Mobility. Japanese Journal of Applied Physics, 2007, 46, L599-L601.	0.8	80
38	Dislocation-Free m-Plane InGaN/GaN Light-Emitting Diodes on m-Plane GaN Single Crystals. Japanese Journal of Applied Physics, 2006, 45, L1197-L1199.	0.8	127
39	Blue-Green InGaN/GaN Laser Diodes on Miscut m-Plane GaN Substrate. Applied Physics Express, 0, 2, 082102.	1.1	56
40	Nonpolar AlGaIn-Cladding-Free Blue Laser Diodes with InGaIn Waveguiding. Applied Physics Express, 0, 2, 071003.	1.1	37